

Docket No.: GR 99 P 5374

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Nicolas Nagel et al.  
RCE of  
Applic. No. : 09/729,069, filed December 4, 2000  
RCE filed : March 4, 2003  
Title : Microelectronic Structure and Method of Fabricating it  
Examiner : David Vu - Art Unit: 2818

INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. 1.97(b)(4)

Hon. Commissioner of Patents and Trademarks,  
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.97(b)(4), copies of the following patents and/or publications are submitted herewith:

Aoyama et al.: "Interfacial Layers between Si and Ru Films Deposited by Sputtering in Ar/O<sub>2</sub> Mixture Ambient", Jpn. J. Applied Physics, Volume 37, 1998, pp. L242-44;

Onishi et al.: "High Temperature Barrier Electrode Technology for High Density Ferroelectric Memories with Stacked Capacitor Structure", J. Electrochemical Society, Volume 145, No. 7, July 1998, pp. 2563-64;

Onishi et al.: "A New High Temperature Electrode-Barrier Technology on High Density Ferroelectric Capacitor Structure", IEDM 96, pp. 699-702;

Kudo et al.: "A High Stability Electrode Technology for Stacked SrBi<sub>2</sub>Ta<sub>2</sub>O<sub>9</sub> capacitors Applicable to Advanced Ferroelectric Memory", IEDM 96, pp. 609-12;

Cho et al.: "Preparation and Characterization of Iridium Oxide Thin Films Grown by DC Reactive Sputtering", Jpn. J. Applied Physics, Volume 36, 1997, pp. 1722-27;

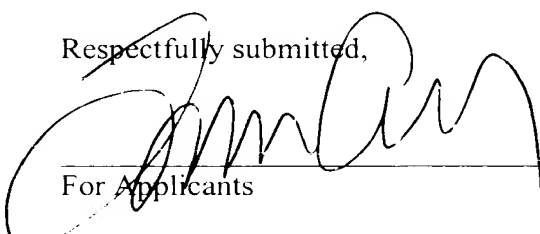
Jeon et al.: "Thermal Stability of Ir/Polycrystalline-Si Structure for Bottom Electrode of Integrated Ferroelectric Capacitors", Applied Physics Letter 71 (4), July 28, 1997, pp. 467-69;

Bhatt et al.: "Novel High Temperature Multilayer Electrode-Barrier Structure for High-Density Ferroelectric Memories", Applied Physics Letter 71 (5), August 1997, pp. 719-21;

Saenger et al.: "Buried, Self-Aligned Barrier Layer Structures for Perovskite-Based Memory Devices Comprising Pt or Ir Bottom Electrodes on Silicon-Contributing Substrates", J. Applied Physics, 83 (2), January 15, 1998, pp. 802-813.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,

  
For Applicants

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